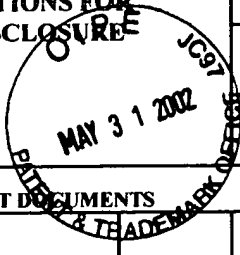


FOR PTO-1449 (Modified)
**LIST OF PATENTS AND PUBLICATIONS FOR
 APPLICANTS INFORMATION DISCLOSURE
 STATEMENT**

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APPLICANT
 SOMIT TALWAR, et al.

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 2812

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER								DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
dt	A	6	2	7	4	4	8	8		8-14-01	Talwar, et al.	438	655	4-12-00

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER								DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
														YES	NO

OTHER

ART (Including Author, Title, Date, Pertinent Pages, Etc.)

dt	B	Somit Talwar, Gaurav Verma, Kurt Weiner, <i>Ultra-Shallow, Abrupt, and Highly-Activated Junctions by Low-Energy Ion Implantation and Laser Annealing</i> , IEEE, 1999, pp. 1171-1174
dt	C	P.S. Peercy, J. Y. Tsao, S. R. Stiffler and Michael O. Thompson, <i>Explosive Crystallization in Amorphous Si Initiated by Long Pulse Width Laser Irradiation</i> , Appl. Phys. Lett. 52 (3), January 18, 1988, pp 203-205

EXAMINER

DATE CONSIDERED

12-08-02

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.